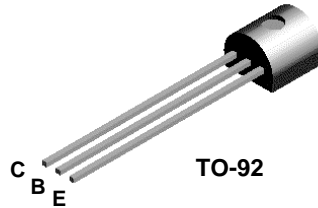
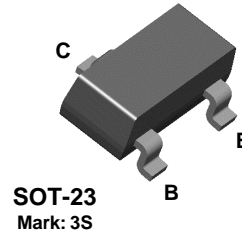


2N5551



MMBT5551



NPN General Purpose Amplifier

This device is designed for general purpose high voltage amplifiers and gas discharge display drivers.

Absolute Maximum Ratings*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	160	V
V _{CBO}	Collector-Base Voltage	180	V
V _{EBO}	Emitter-Base Voltage	6.0	V
I _C	Collector Current - Continuous	600	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5551	*MMBT5551	
P _D	Total Device Dissipation Derate above 25°C	625	350	mW
		5.0	2.8	mW/°C
R _{θJC}	Thermal Resistance, Junction to Case	83.3		°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	200	357	°C/W

* Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

NPN General Purpose Amplifier

(continued)

Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Sustaining Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	160		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 100 \text{ } \mu\text{A}, I_E = 0$	180		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	6.0		V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 120 \text{ V}, I_E = 0,$ $V_{CB} = 120 \text{ V}, I_E = 0, T_A = 100^\circ\text{C}$		50 50	nA μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_C = 0$		50	nA

ON CHARACTERISTICS

h_{FE}	DC Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V}$ $I_C = 50 \text{ mA}, V_{CE} = 5.0 \text{ V}$	80 80 30	250	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.15 0.20	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		1.0 1.0	V V

SMALL SIGNAL CHARACTERISTICS

f_T	Current Gain - Bandwidth Product	$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 100 \text{ MHz}$	100	300	MHz
C_{obo}	Output Capacitance	$V_{CB} = 10 \text{ V}, I_E = 0,$ $f = 1.0 \text{ MHz}$		6.0	pF
C_{ibo}	Input Capacitance	$V_{BE} = 0.5 \text{ V}, I_C = 0,$ $f = 1.0 \text{ MHz}$		20	pF
h_{fe}	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$ $f = 1.0 \text{ kHz}$	50	250	
NF	Noise Figure	$I_C = 250 \text{ } \mu\text{A}, V_{CE} = 5.0 \text{ V},$ $R_S = 1.0 \text{ k}\Omega, f = 10 \text{ Hz to } 15.7 \text{ kHz}$		8.0	dB

*Pulse Test: Pulse Width $\leq 300 \text{ } \mu\text{s}$, Duty Cycle $\leq 2.0\%$ **Spice Model**

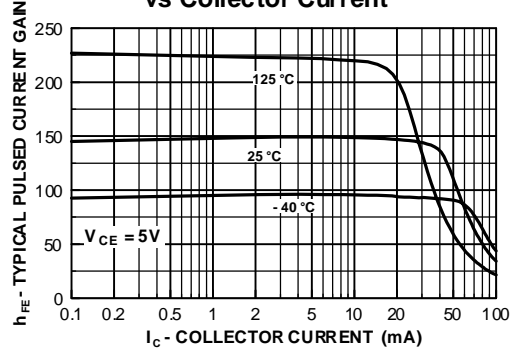
NPN (Is=2.511f Xti=3 Eg=1.11 Vaf=100 Bf=242.6 Ne=1.249 Ise=2.511f Ikf=.3458 Xtb=1.5 Br=3.197 Nc=2 Isc=0
Ikr=0 Rc=1 Cjc=4.883p Mjc=.3047 Vjc=.75 Fc=.5 Cje=18.79p Mje=.3416 Vje=.75 Tr=1.202n Tf=560p Itf=50m
Vtf=5 Xtf=8 Rb=10)

NPN General Purpose Amplifier (continued)

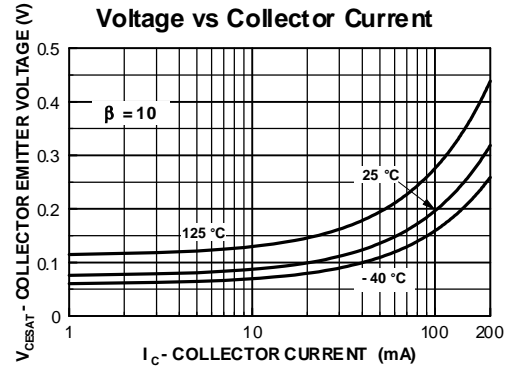
2N5551 / MMBT5551

Typical Characteristics

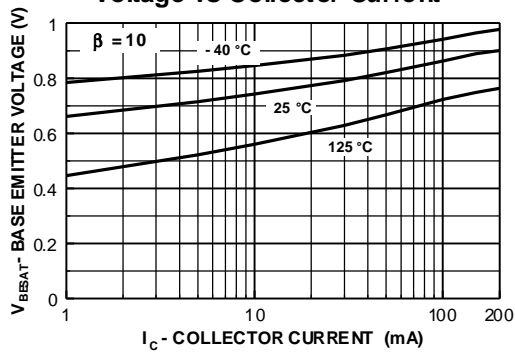
Typical Pulsed Current Gain
vs Collector Current



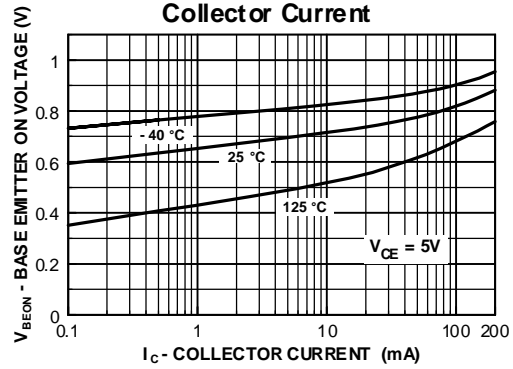
Collector-Emitter Saturation
Voltage vs Collector Current



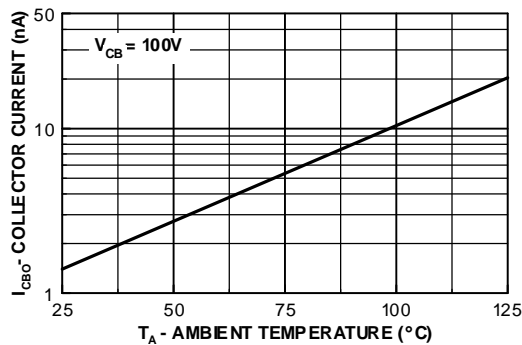
Base-Emitter Saturation
Voltage vs Collector Current



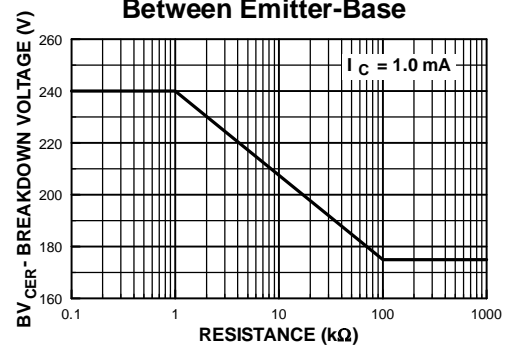
Base Emitter ON Voltage vs
Collector Current



Collector-Cutoff Current
vs. Ambient Temperature



Collector-Emitter Breakdown
Voltage with Resistance
Between Emitter-Base



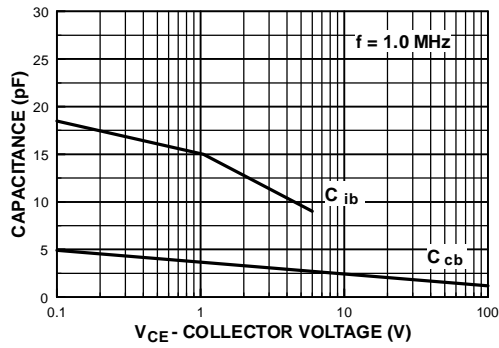
NPN General Purpose Amplifier

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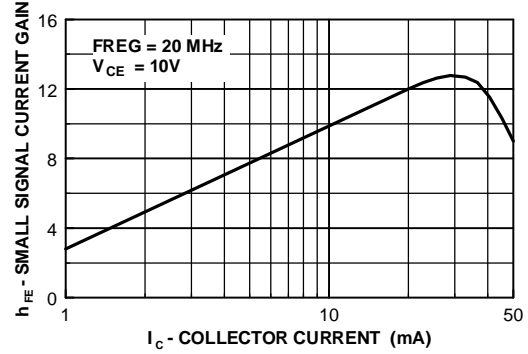
2N5551 / MMBT5551

Typical Characteristics (continued)

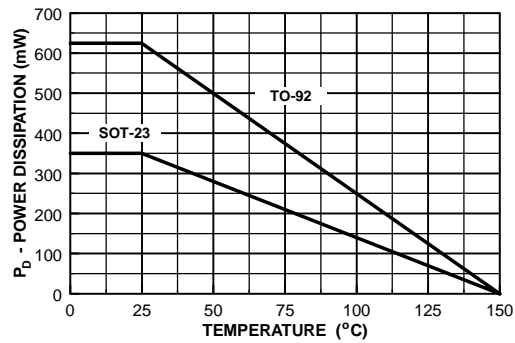
Input and Output Capacitance
vs Reverse Voltage



Small Signal Current Gain
vs Collector Current



Power Dissipation vs
Ambient Temperature



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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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